

WHAT IS CLAIMED IS:

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1. A semiconductor device comprising:
a semiconductor substrate;
at least two semiconductor components provided on the principal surface of the substrate; and
multiple through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate between the at least two components.

2. The device of Claim 1, wherein a gap between two adjacent ones of the through holes is smaller than the thickness of the substrate.

3. The device of Claim 1 further comprising a conductor film formed on the side faces of the through holes.

4. The device of Claim 3 further comprising a grounded wiring layer provided on the backside of the substrate,
wherein the conductor film is connected to the grounded wiring layer.

5. The device of Claim 1, wherein each of the components is a power-amplifying transistor for a radio frequency signal.

6. A semiconductor device comprising:

- a semiconductor substrate;
- at least two semiconductor components provided on the principal surface of the substrate;
- electrodes of the at least two components provided on the substrate;
- a first group of through holes, which pass from the principal surface through the backside of the substrate and are provided in respective regions of the substrate under the electrodes;
- a first conductor film provided on the side faces of the first group of through holes;
- a second group of through holes, which pass from the principal surface through the backside of the substrate and are provided in a region of the substrate between the components;
- a second conductor film provided on the side faces of the second group of through holes; and
- a wiring layer, which is provided on the backside of the substrate and is in contact with the first and second conductor films.

7. The device of Claim 6, wherein each of the components is a power-amplifying transistor for an RF signal.